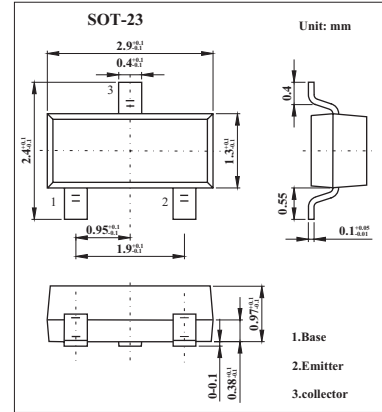


**PNP Transistor**  
**BC856A,B/BC857A,B,C/BC858A,B,C**

■ Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	BC856	-80	V
	BC857	-50	
	BC858	-30	
Collector-Emitter Voltage	BC856	-65	V
	BC857	-45	
	BC858	-30	
Emitter-Base Voltage	VEBO	-5	V
Collector Current -Continuous	IC	-0.1	A
Collector Power Dissipation	PC	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-65 to +150	°C



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SMD Type

Transistors

BC856A,B/BC857A,B,C/BC858A,B,C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Collector-base breakdown voltage	BC856	$I_c = -10\mu A, I_E = 0$	-80			V	
	BC857		-50				
	BC858		-30				
Collector-emitter breakdown voltage	BC856	$I_c = -10\text{ mA}, I_B = 0$	-65			V	
	BC857		-45				
	BC858		-30				
Emitter-base breakdown voltage	VEBO	$I_E = -10\mu A, I_C = 0$	-5			V	
Collector cut-off current	BC856	ICBO	$V_{CB} = -70\text{ V}, I_E = 0$			-0.1	$\mu\text{ A}$
	BC857		$V_{CB} = -45\text{ V}, I_E = 0$				
	BC858		$V_{CB} = -25\text{ V}, I_E = 0$				
Collector cut-off current	BC856	ICEO	$V_{CE} = -60\text{ V}, I_B = 0$			-0.1	$\mu\text{ A}$
	BC857		$V_{CE} = -40\text{ V}, I_B = 0$				
	BC858		$V_{CE} = -25\text{ V}, I_B = 0$				
Emitter cut-off current	IEBO	$V_{EB} = -5\text{ V}, I_C = 0$			-0.1	$\mu\text{ A}$	
DC current gain	BC856A, 857A, 858A	hFE	$V_{CE} = -5\text{ V}, I_C = -2\text{ mA}$	120		250	
	BC856B, 857B, 858B			220		475	
	BC857C, BC858C			420		800	
Collector-emitter saturation voltage	VCE(sat)	$I_C = -100\text{ mA}, I_B = -5\text{ mA}$			-0.5	V	
Base-emitter saturation voltage	VBE(sat)	$I_C = -100\text{ mA}, I_B = -5\text{ mA}$			-1.1	V	
Collector capacitance	Cob	$V_{CB} = -10\text{ V}, f = 1\text{ MHz}$			4.5	pF	
Transition frequency	fr	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}, f = 100\text{ MHz}$	100			MHz	

■ Marking

NO.	BC856A	BC856B
Marking	3A	3B

NO.	BC857A	BC857B	BC857C
Marking	3E	3F	3G

NO.	BC858A	BC858B	BC858C
Marking	3J	3K	3L



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SMD Type Transistors

BC856A,B/BC857A,B,C/BC858A,B,C

Typical Characteristics

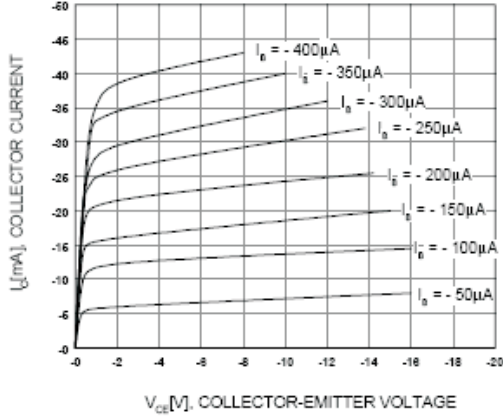


Fig.1 Static Characteristic

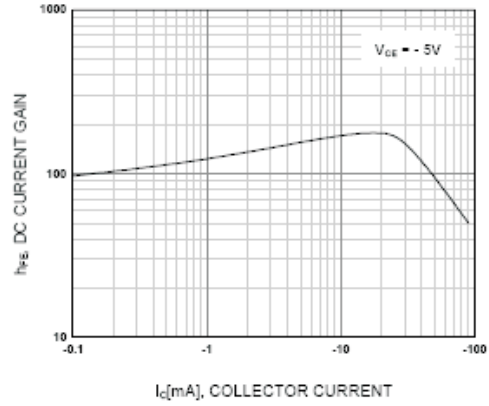


Fig.2 DC Current Gain

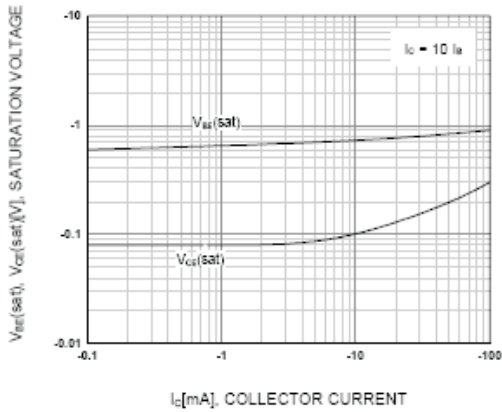


Fig.3 Base Emitter Saturation Voltage  
Collector Emitter Saturation Voltage

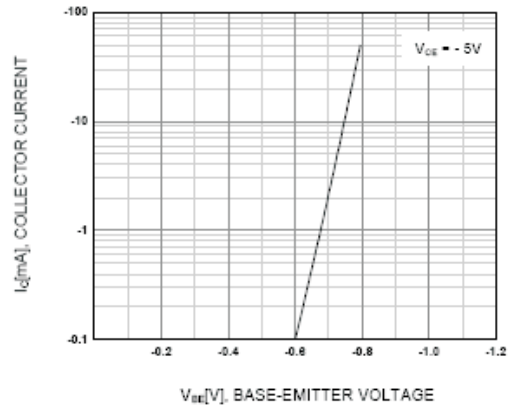


Fig.4 Base Emitter ON Voltage

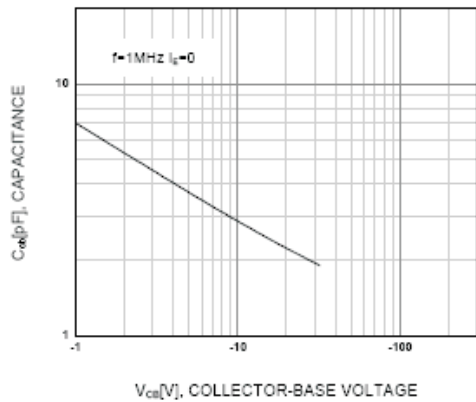


Fig.5 Collector Output Capacitance

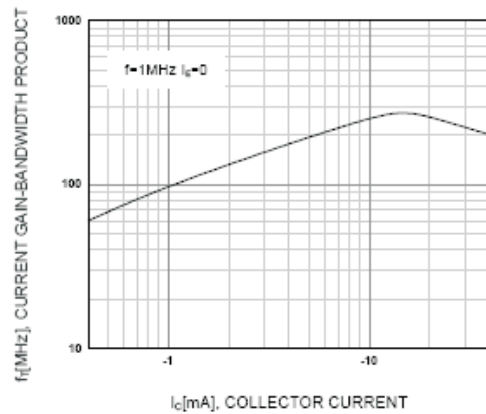


Fig.6 Current Gain Bandwidth Product